



FUKUCOM COMPANY LTD.

福靈有限公司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.
TEL: 852-2790 0314 FAX: 852-2790 0206

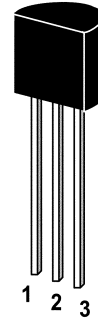
ST 2SC2458

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into four groups, O, Y, G and L, according to its DC current gain.

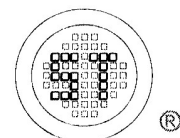
On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (Ta=25°C)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	150	mA
Base Current	I_B	50	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_s	-55 to +125	°C



SEMTECH

Dated : 25/12/2002



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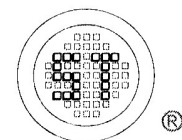
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Characteristics at T_{amb}=25 °C

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V _{CE} =6V, I _C =2mA					
Current Gain Group O	h _{FE}	70	-	140	-
Y	h _{FE}	120	-	240	-
G	h _{FE}	200	-	400	-
L	h _{FE}	350	-	700	-
Collector Cutoff Current at V _{CB} =50V	I _{CBO}	-	-	0.1	μA
Emitter Cutoff Current at V _{EB} =5V	I _{EBO}	-	-	0.1	μA
Collector Emitter Saturation Voltage at I _C =100mA, I _B =10mA	V _{CE(sat)}	-	0.10	0.25	V
Transition Frequency at V _{CE} =10V, I _C =1mA	f _T	80	-	-	MHz
Noise Figure at V _{CE} =6V, I _C =0.1mA f=1KHz, R _g =10KΩ	NF	-	1.0	10	dB
Collector Output Capacitance at V _{CB} =10V, f=1MHz	C _{OB}	-	2.0	3.5	pF



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